

**AMENDMENTS TO THE CLAIMS**

1. (currently amended) A semiconductor device, comprising:

a first implant region having a first conductivity type, said first implant region formed on a semiconductor substrate with a first implant mask layer comprising a silicon antireflective coating layer; and

a second implant region having a second conductivity type, said second region formed on said semiconductor substrate with a second implant mask layer, said first implant mask layer having an etch selectivity with respect to said second implant mask layer;

wherein said first and said second implant regions are self-aligned with respect to one another.

2. (original) The semiconductor device of claim 1, wherein said first implant region is formed following a lithographic patterning step and said second implant region is formed following a non-lithographic, image reversal step.

3. (new) The semiconductor device of claim 2, wherein said silicon antireflective coating layer is formed upon an etch stop layer initially formed upon said substrate.

4. (new) The semiconductor device of claim 3, wherein said etch stop layer further comprises a first organic antireflective coating layer, and said second implant mask layer further comprises a second organic antireflective coating layer.